



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	7mΩ @ V <sub>GS</sub> = 10V	14.1A
30V	10mΩ @ V <sub>GS</sub> = 4.5V	11.8A
	15mΩ @ V <sub>GS</sub> = 3.7V	9.6A

# **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**

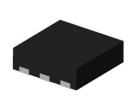
### **Features**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

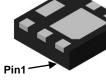
### **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)

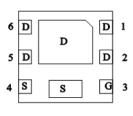
#### U-DFN2020-6 (Type F)



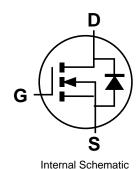
Top View



**Bottom View** 



Pin Out **Bottom View** 



Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMT3006LFDF-7	7	3,000
DMT3006LFDF-13	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

Site 1



6M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	201	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н		1	,	J	K		L		M
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



6M= Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 9 = 2019)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	1
Code	9	0	1	2	3	4	5	6	l

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	30	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V Steady State		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	14.1 12.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	80	Α
Continuous Source-Drain Diode Current (Note 6) T <sub>A</sub> = +25°C			Is	2	Α
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	25	Α
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	31	mJ

### **Thermal Characteristics**

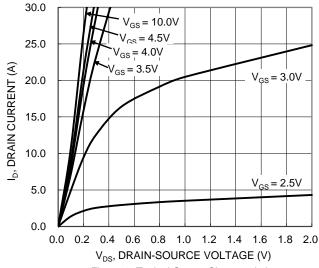
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	155	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	60	°C/W
Thermal Resistance, Junction to Case (Note 6)	T <sub>C</sub> = +25°C	Rejc	6.9	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

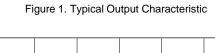
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	1	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (T <sub>J</sub> = +25°C)	I <sub>DSS</sub>	_	I	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			5.8	7		$V_{GS} = 10V, I_D = 9A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	7.8	10	mΩ	$V_{GS} = 4.5V, I_D = 8A$	
			9.3	15		$V_{GS} = 3.7V, I_D = 5A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.0	V	$V_{GS} = 0V$ , $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	1,155	_		45)/ )/ 0)/	
Output Capacitance	Coss	_	456	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	72	_		1 = 1.000112	
Gate Resistance	$R_{G}$	_	1.6	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	_	8.4	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	16.7	_	nC	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q <sub>GS</sub>	_	2.2	_	nc nc	$V_{DD} = 15V, I_D = 9A$	
Gate-Drain Charge	$Q_{GD}$	_	3.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_			
Turn-On Rise Time	t <sub>R</sub>	_	5.5	_	20	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	13.5	_	ns	$R_G = 3\Omega$ , $I_D = 9A$	
Turn-Off Fall Time	t <sub>F</sub>	_	4.6	_			
Reverse Recovery Time	t <sub>RR</sub>	_	19.3	_	ns	1 4 5 4 -11/-14 4000 / 1	
Reverse Recovery Charge	$Q_{RR}$		8.6	_	nC	I <sub>F</sub> = 1.5A, di/dt = 100A/μs	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J} = +25^{\circ}C$ .
  - 8. Short duration pulse test used to minimize self-heating effect.
  - 9. Guaranteed by design. Not subject to product testing.







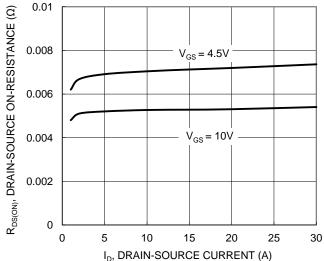


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

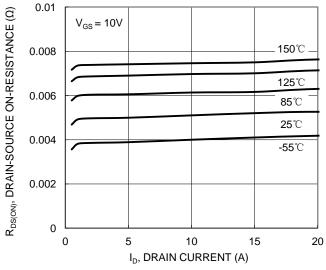


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

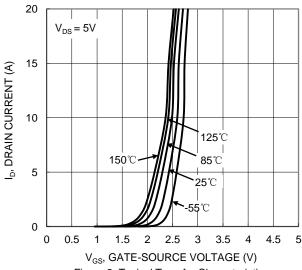


Figure 2. Typical Transfer Characteristic

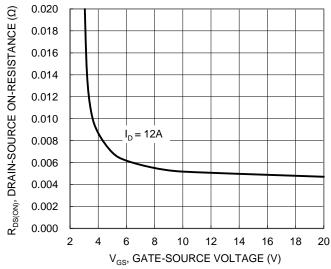


Figure 4. Typical Transfer Characteristic

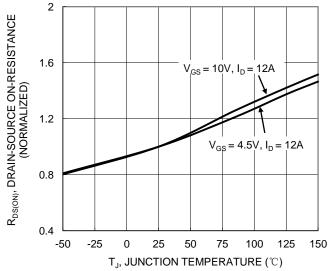


Figure 6. On-Resistance Variation with Temperature





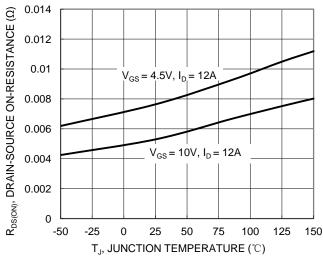


Figure 7. On-Resistance Variation with Temperature

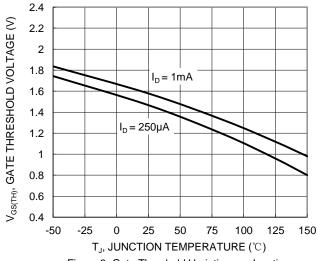


Figure 8. Gate Threshold Variation vs. Junction Temperature

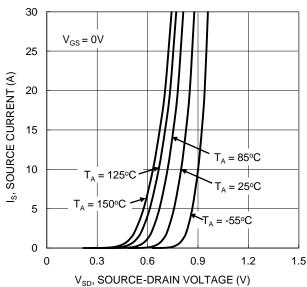
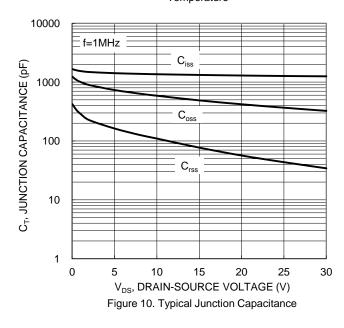
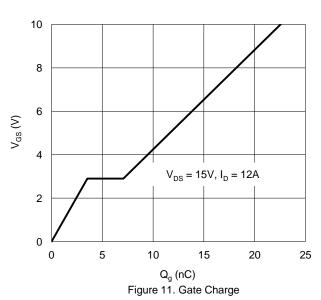
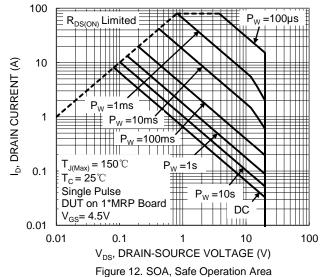


Figure 9. Diode Forward Voltage vs. Current









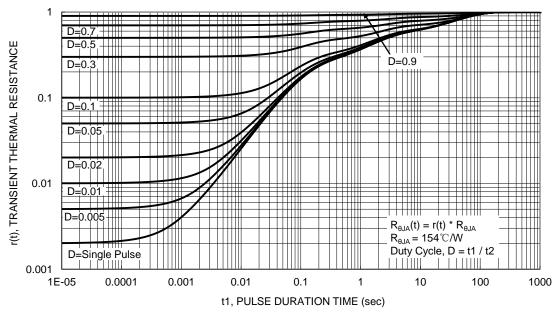


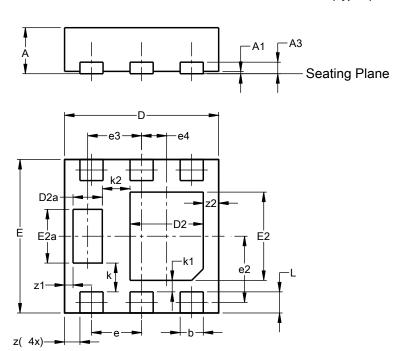
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

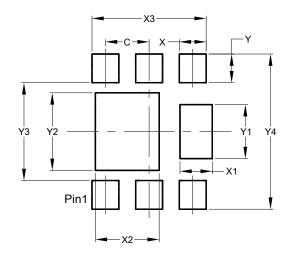


U-DFN2020-6									
	(Type F)								
Dim	Min	Max	Тур						
Α	0.57	0.63	0.60						
A1	0.00	0.05	0.03						
A3	-	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33 0.43 0.38								
Е	1.95 2.05 2.00								
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е		0.65 BS	С						
e2		).863 BS	SC						
е3		0.70 BS	С						
e4		).325 BS	SC						
k		0.37 BS	С						
k1		0.15 BS	С						
k2	0.36 BSC								
L	0.225 0.325 0.275								
Z	0.20 BSC								
<b>z</b> 1	0.110 BSC								
z2		0.20 BS	C						
All C	imens	ions in	mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-6 (Type F)



Dimensions	Value
Dimensions	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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